模拟与数模混合集成电路

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Table 4.1

Parameter Symbol	Parameter Description	Typical Parameter Value		
		n-Channel	p-Channel	Units
V _{T0}	Threshold voltage $(V_{BS} = 0)$	0.7 ± 0.15	-0.7 ± 0.15	v
<i>K'</i>	Transconductance parameter (in saturation)	110.0 ± 10%	$50.0 \pm 10\%$	μ.Α/V ²
γ	Bulk threshold parameter	.0.4	0.57	$V^{1/2}$
λ	Channel length modulation parameter	$0.04 (L = 1 \mu m)$ $0.01 (L = 2 \mu m)$	$0.05 (L = 1 \mu m)$ $0.01 (L = 2 \mu m)$	V-1
$2 \phi_F $	Surface potential at strong inversion	0.7	0.8	V

4.1 Calculate the output resistance and the minimum output voltage, while maintaining all devices in saturation, for the circuits shown in Figure 4.1. Assume that i_{OUT} is actually 10μ A. Use Table 4.1 for device model information.

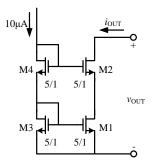


Fig 4.1

解:

$$V_{GS3} = V_{G3} = \sqrt{\frac{2i_D}{\beta}} + V_T = \sqrt{\frac{2 \times 10 \times 10^{-6}}{5 \times 110 \times 10^{-6}}} + 0.7 = \sqrt{\frac{20}{550}} + 0.7 = 0.891$$

$$V_{SB2} = V_{G3} = 0.891$$

 $V_{DS1} = V_{G3} + V_{GS4} - V_{GS2}$ because all devices are matched.

$$g_{m2} = g_{m4} \cong \sqrt{(2K'W/L)|I_D|} = \sqrt{2\times110\times10^{-6}\times5/1\times10\times10^{-6}} = 104.9\times10^{-6}$$

$$g_{mbs2} = g_{mbs4} = g_{m2} \frac{\gamma}{2(2|\phi_F| + V_{SB})^{1/2}} = 104.9 \times 10^{-6} \frac{0.4}{2(0.7 + 0.891)^{1/2}} = 16.63 \times 10^{-6}$$

$$r_{\text{out}} = \frac{v_{\text{out}}}{i_{\text{out}}} = r_{ds1} + r_{ds2} + [(g_{m2} + g_{mbs2})r_{ds2}] r_{ds1}$$

$$g_{ds1} = g_{ds2} \cong I_D \lambda = 10 \times 10^{-6} \times 0.04 = 400 \times 10^{-9}$$

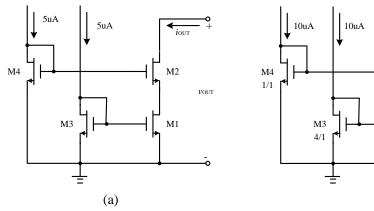
$$r_{ds1} = r_{ds2} = \frac{1}{g_{ds}} = 2.5 \times 10^6$$

$$r_{\text{out}} = 2.5 \times 10^6 + 2.5 \times 10^6 + [(104.9 \times 10^{-6} + 16.63 \times 10^{-6}) \ 2.5 \times 10^6] \ 2.5 \times 10^6$$

$$r_{\text{out}} = 764 \times 10^6$$

$$\begin{split} v_{out(\text{min})} &= V_{GS3} + V_{GS4} - V_{T2} = V_{GS3} + \sqrt{\frac{2i_D}{\beta}} + V_{T4} - V_{T2} \\ &= V_{GS3} + \sqrt{\frac{2i_D}{\beta}} = 0.891 + \sqrt{\frac{2 \times 10 \times 10^{-6}}{5 \times 110 \times 10^{-6}}} = 1.082 \text{V} \end{split}$$

4.2 Design M3 and M4 of Figure 4.2(a) so that the output characteristics are identical to the circuit shown in Figure 4.2(b). It is desired that i_{OUT} is ideally 10uA.



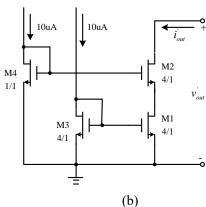


Figure 4.2

解:

For getting
$$i_{out} = i_{out} = 10 \mu A$$

In Fig.4.2a), ::
$$i_3 = i_4 = 5\mu A$$

Thus to ensure
$$i_{out} = 10 \mu A$$

We must have
$$\left(\frac{W}{L}\right)_1 = 2\left(\frac{W}{L}\right)_3$$

$$\left(\frac{W}{L}\right)_3 = \frac{1}{2} \left(\frac{W}{L}\right)_1 = \frac{1}{2} \cdot \frac{4}{1} = \frac{2}{1}$$

In Fig. 4.2b) $i_4 = i_3 = i_1$

$$\left(\frac{W}{L}\right)_{4} \Delta V_{4}^{2} = \left(\frac{W}{L}\right)_{1} \Delta V_{1}^{2} \Rightarrow \left(\frac{1}{1}\right) \Delta V_{4}^{2} = \left(\frac{4}{1}\right) \Delta V_{1}^{2}$$

$$\therefore \frac{\Delta V_4^2}{\Delta V_1^2} = \frac{4}{1} \Longrightarrow \Delta V_4 = 2\Delta V_1$$

$$V_{G4} = V_T + 2\Delta V_1$$

$$V_{G2} = V_{G4} = V_T + 2\Delta V_1$$

$$\therefore V_{MIN} = 2\Delta V_1$$

And we get V_{MIN} in Fig.5.2(a): $V_{\text{MIN}} = 2\Delta V_1$

$$\therefore V_{G2} = V_{G4} = V_T + 2\Delta V_1 \text{ and } \Delta V_4 = 2\Delta V_1$$

In Fig.5.2(a):
$$i_4 = i_3 = \frac{1}{2}i_1$$

$$\left(\frac{W}{L}\right)_4 \Delta V_4^2 = \frac{1}{2} \left(\frac{W}{L}\right)_1 \Delta V_1^2$$

$$\left(\frac{W}{L}\right)_{4} = \frac{1}{2} \left(\frac{W}{L}\right)_{1} \left(\frac{\Delta V_{1}}{\Delta V_{4}}\right)^{2}$$

For
$$\left(\frac{\Delta V_4}{\Delta V_1}\right)^2 = 4 \Longrightarrow \left(\frac{\Delta V_1}{\Delta V_4}\right)^2 = \frac{1}{4}$$

$$\left(\frac{W}{L}\right)_4 = \frac{1}{8} \left(\frac{W}{L}\right)_1 = \frac{1}{8} \cdot \frac{4}{1} = \frac{1}{2}$$

4.3 A reference circuit is shown in figure 4.3, assume that $(W/L)_1=(W/L)_2=(W/L)_3=4$, $(W/L)_4=1$, please calculate the expression of V_{REF} .

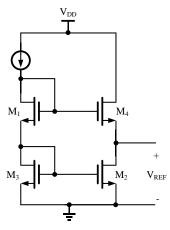


Figure 4.3

解:

 V_{T}

4.4 As the circuits shown in Figure 4.4, I_{REF} =0.3mA and γ =0. Using the model parameters in Table 4.1,

(a)Calculate the voltage V_b when $V_X=V_Y$;

(b) If V_b is 100mV smaller than the value in (a), calculate the deviation of I_{out} from 300 μ A.

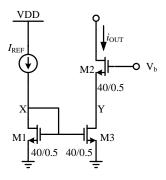


Figure 4.4

解:

a)

$$V_{GS1} = V_T + \sqrt{\frac{2I_{REF}}{K_N '(W/L)_1}} = 0.7 + \sqrt{\frac{2 \times 0.3 \times 10^{-3}}{80 \times 110 \times 10^{-6}}} = 0.961V$$

$$V_b = 2V_{GS1} = 1.922V$$

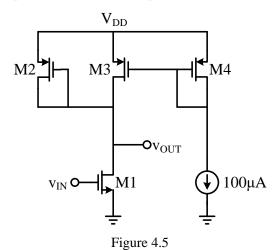
b)

$$\lambda(l = 0.5u) \approx \lambda(l = 1u) \frac{1u}{0.5u} = 0.04 \times 2 = 0.08V^{-1}$$

$$I_{out} = I_{REF} \, \frac{1 + \lambda (V_{GS1} + \Delta V_b)}{1 + \lambda V_{GS1}} \label{eq:out}$$

$$\Delta I_{out} = I_{REF} \frac{\lambda \Delta V_b}{1 + \lambda V_{GS1}} = 0.3 \times 10^{-3} \times \frac{0.08 \times (-0.1)}{1 + 0.08 \times 0.961} = -2.229 \times 10^{-6} A$$

4.5 Assume that W/L ratios of Figure 4.5 are $(W/L)_1 = 2\mu m/1\mu m$ and $(W/L)_2 = (W/L)_3 = (W/L)_4$ = $1\mu m/1\mu m$. Find the dc value of v_{IN} that will give a dc current in M1 of 110 μ A. Calculate the small signal voltage gain and output resistance using the parameters of Table 4.1. Assume $\lambda = \gamma = 0$.



Solution:

$$I_{D1} = \frac{1}{2} K_N' (\frac{W}{L})_1 (V_{in} - V_{TH1})^2$$

$$110\mu = \frac{1}{2} \times (110\mu) \times \frac{2}{1} \times (V_{in} - 0.7)^2$$

$$V_{in} = 1.7V$$

$$\begin{split} I_{D3} &= I_{D4} = 100 \mu A \\ I_{D2} &= I_{D1} - I_{D3} = 10 \mu A \\ A_{_{V}} &\cong -\frac{g_{m1}}{g_{m2}} = -\sqrt{\frac{K'_{_{N}}}{K'_{_{P}}}} \frac{(W/L)_{_{1}}}{(W/L)_{_{2}}} \frac{I_{D1}}{I_{D2}} = -\sqrt{\frac{110\mu}{50\mu}} \times \frac{2}{1} \times \frac{110\mu}{10\mu} = -6.96V/V \\ R_{out} &\cong \frac{1}{g_{m2}} = \frac{1}{\sqrt{2K'_{_{P}}(W/L)_{_{2}}I_{_{D2}}}} = \frac{1}{\sqrt{2\times50\times10^{-6}\times1\times10\times10^{-6}}} = 31.6K\Omega \end{split}$$